



Absolute Maximum Ratings @TA=25°C

Parameters	Symbol	Min	Max	Unit
Repetitive peak reverse voltage	V _{RRM}	-	110	V
Continuous reverse voltage	V _R	-	100	V
Continuous forward current	I _F	-	200	mA
Repetitive peak forward current	I _{FRM}		500	mA
Non-repetitive peak forward current @square wave, T _j =125°C prior to surge	I _{FSM}	t=1μs	4	A
		t=1ms	1	A
		t=1s	0.5	A
Total power dissipation(Note 1)	P _{tot}		250	mW
Junction Temperature	T _j	-	150	°C
Storage Temperature	T _{stg}	-65	+150	°C

Note 1: Device mounted on an FR-4 PCB.

Electrical Characteristics @ Tj=25°C unless otherwise specified

Parameters	Symbol	Conditions	Min	Typ.	Max	Unit
Forward voltage	V _F	I _F =1mA	-	-	715	mV
		I _F =10mA	-	-	855	mV
		I _F =50mA	-	-	1	V
		I _F =150mA	-	-	1.25	V
Reverse current	I _R	V _R =25V	-	-	30	nA
		V _R =100V	-	-	1	μA
		V _R =25V, T _j =150°C	-	-	30	μA
		V _R =100V, T _j =150°C	-	-	50	μA
Diode capacitance	C _d	V _R =0V, f=1MHz	-	-	1.5	pF
Reverse recovery time	t _{rr}	when switched from I _F =10mA to I _R =10mA, R _L =100Ω, measured at I _R =1mA	-	-	4	ns
Forward recovery voltage	V _{fr}	when switched from I _F =10mA t _r =20ns	-	-	1.75	V

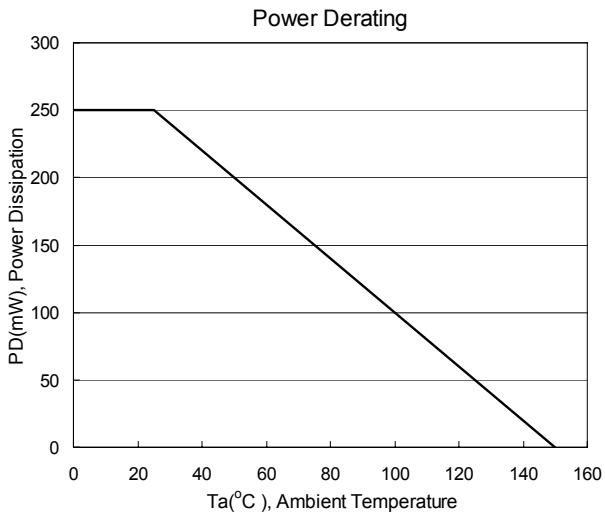
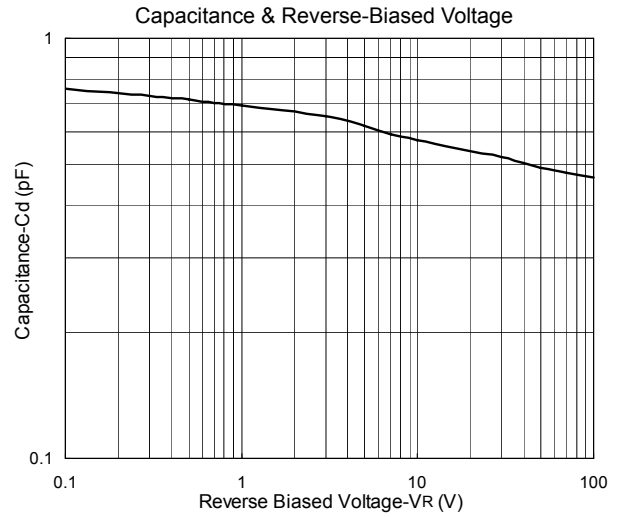
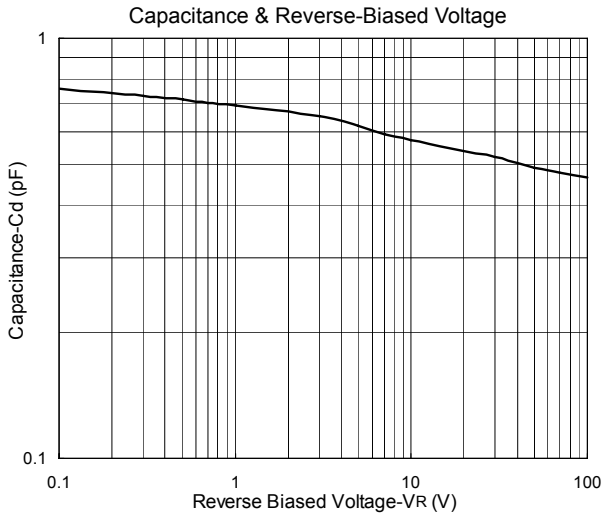
Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
R _{th,j-tp}	thermal resistance from junction to tie-point		360	°C/W
R _{th,j-a}	thermal resistance from junction to ambient	Note 1	500	°C/W

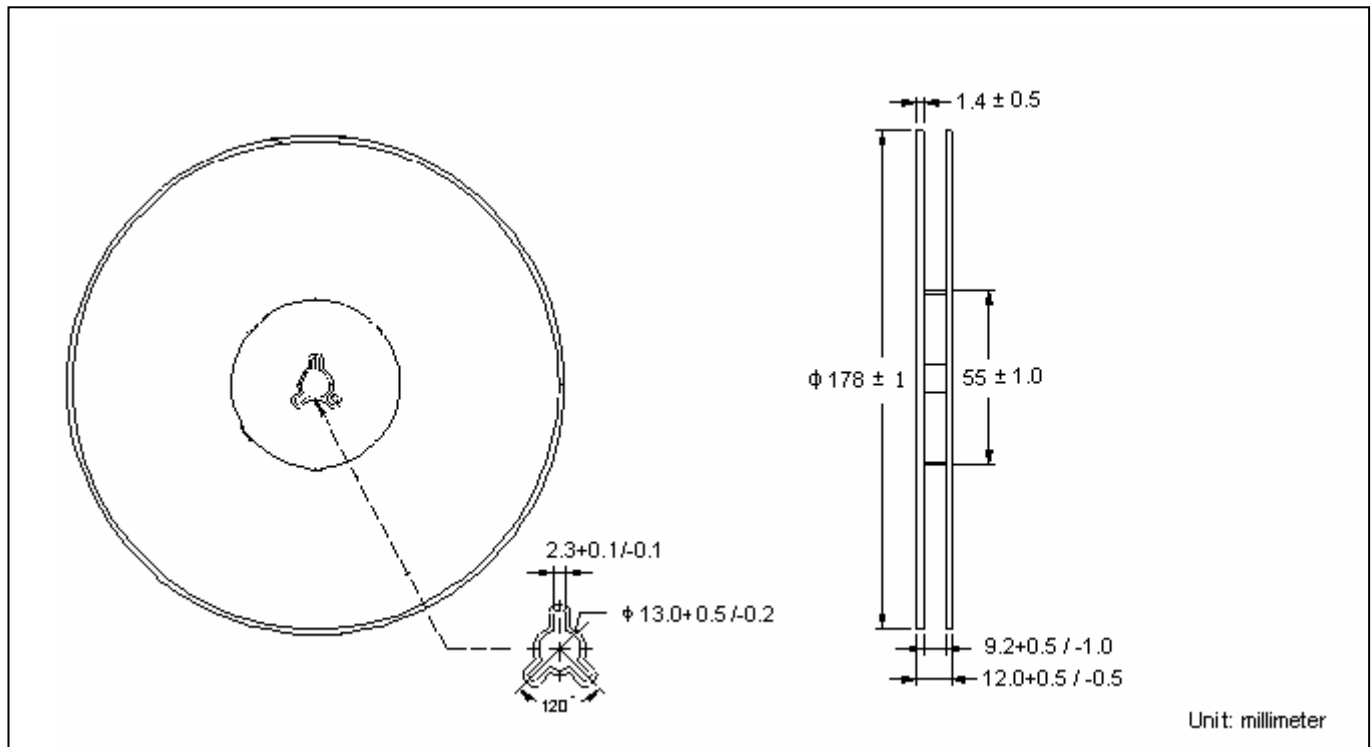
Note 1: Device mounted on an FR-4 PCB.



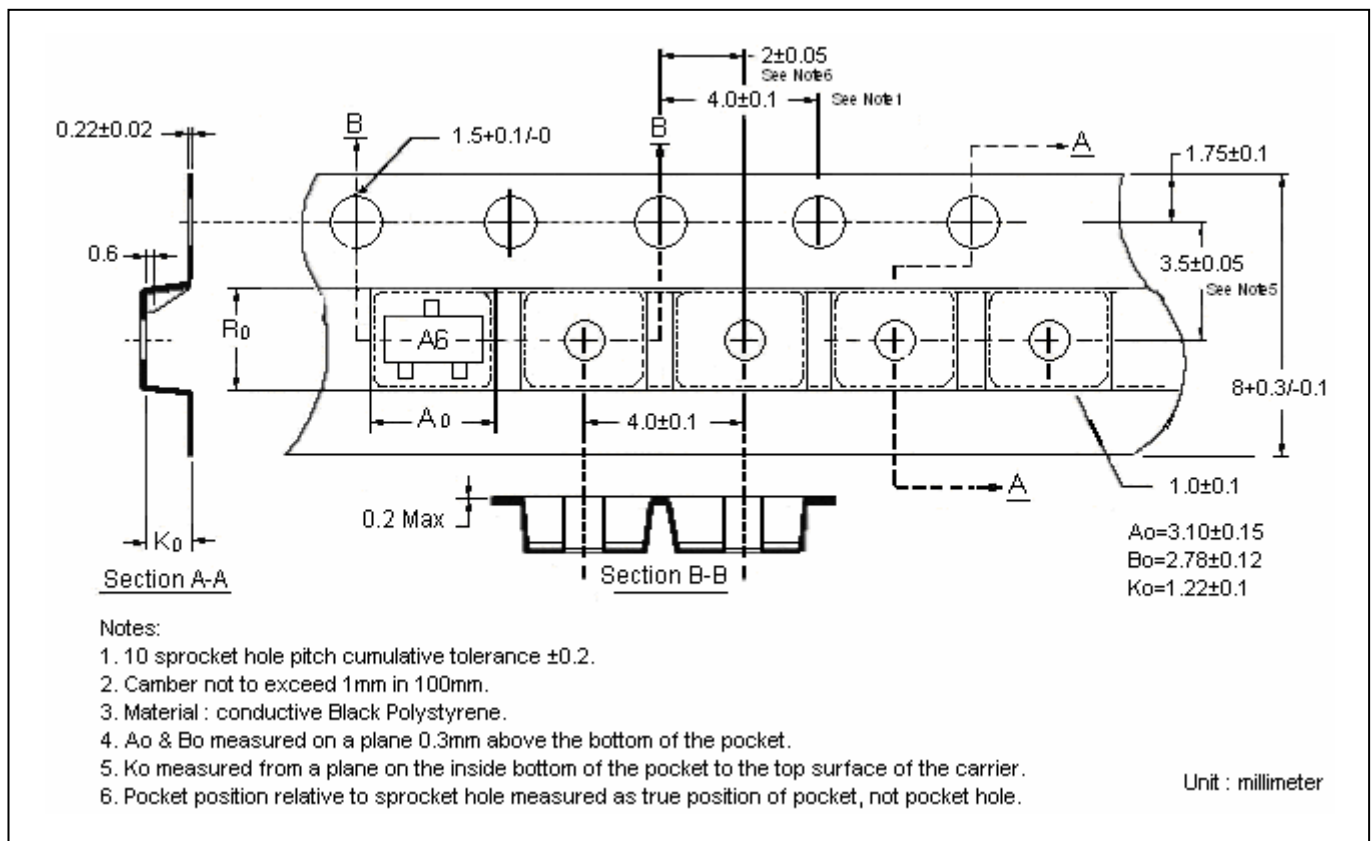
Characteristic Curves



Reel Dimension



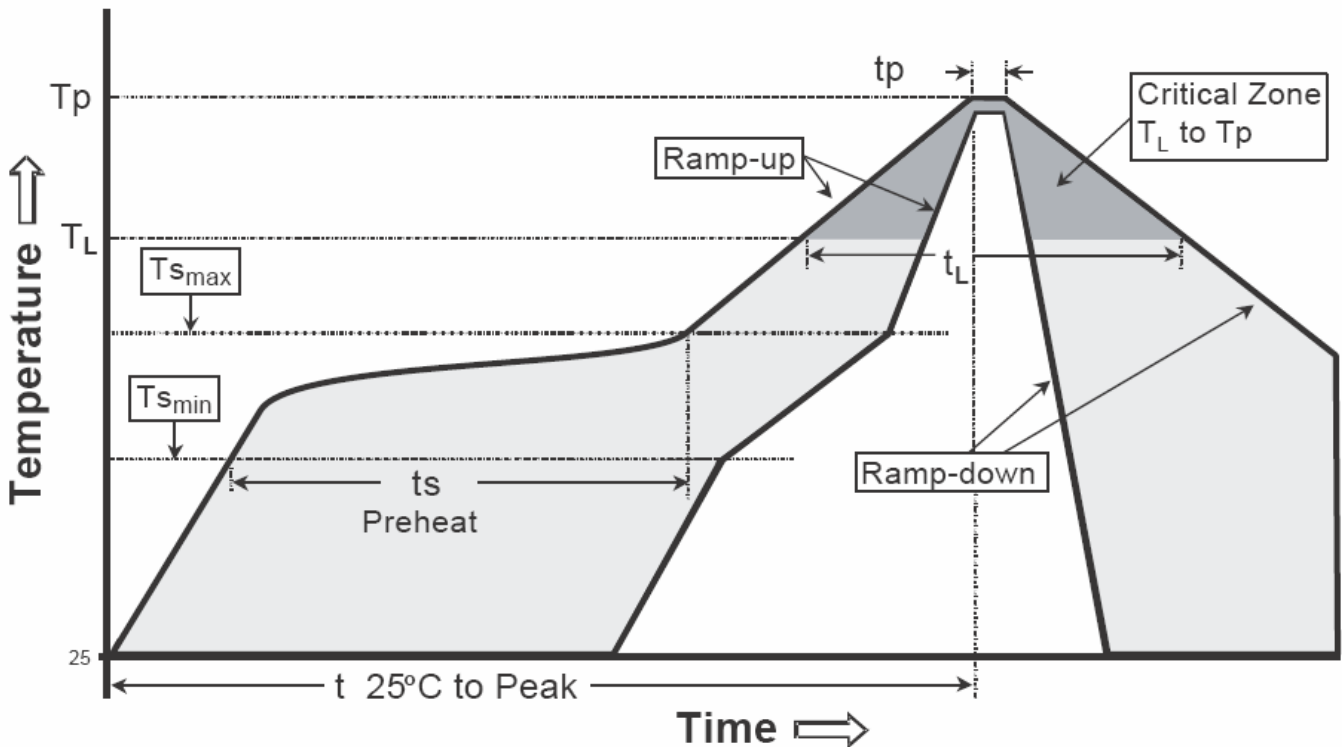
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

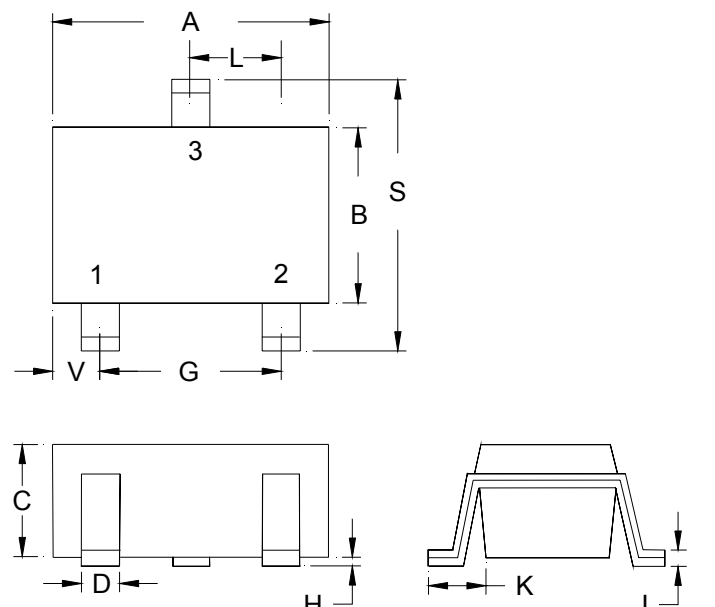
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

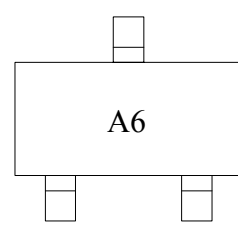
Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



The diagram shows three views of a 3-lead SOT-23 package: a top view with dimensions A, B, C, D, G, H, L, S, and V; a side view with dimensions C, D, and H; and a perspective view with dimensions J and K. The top view labels the leads as 1, 2, and 3.

Marking:



A6

3-Lead SOT-23 Plastic
 Surface Mounted Package
 CYStek Package Code: N3

Style: Pin. 1. Anode 2. Not Connected
 3. Cathode

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes: 1. Controlling dimension: millimeters.
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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